

LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 20 A
V_{RRM}	40 V
$T_j(\text{max})$	150 °C
$V_F(\text{max})$	0.49 V

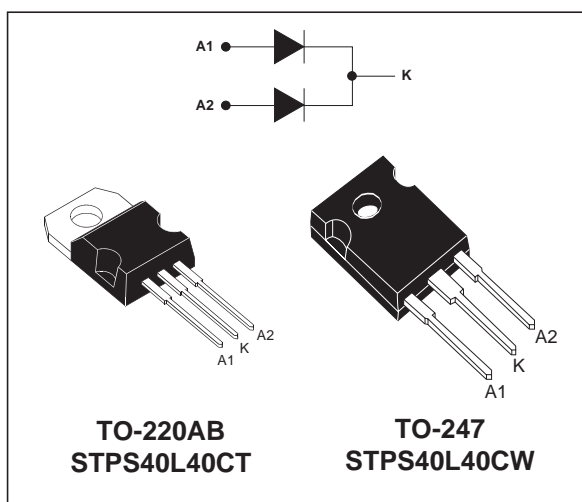
FEATURES AND BENEFITS

- LOW FORWARD VOLTAGE DROP MEANING VERY SMALL CONDUCTION LOSSES
- LOW DYNAMIC LOSSES AS A RESULT OF THE SCHOTTKY BARRIER
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual center tap Schottky barrier rectifier designed for high frequency Switched Mode Power Supplies and DC to DC converters.

Packaged in TO-220AB and TO-247 this device is intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		40	V
$I_{F(RMS)}$	RMS forward current		30	A
$I_{F(AV)}$	Average forward current	$T_c = 130^\circ\text{C}$ $\delta = 0.5$	Per diode: 20 Per device: 40	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	230	A
I_{RRM}	Repetitive peak reverse current	$t_p = 2 \mu\text{s}$ square $F = 1\text{kHz}$	2	A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100 \mu\text{s}$ square	3	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1 \mu\text{s}$ $T_j = 25^\circ\text{C}$	8100	W
T_{stg}	Storage temperature range		- 65 to + 150	°C
T_j	Maximum operating junction temperature *		150	°C
dV/dt	Critical rate of rise of reverse voltage		10000	V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$ thermal runaway condition for a diode on its own heatsink

STPS40L40CT/CW

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.5	$^{\circ}\text{C/W}$
		Total	0.8	
$R_{th(c)}$		Coupling	0.1	$^{\circ}\text{C/W}$

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit	
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			0.8	mA	
		$T_j = 100^{\circ}\text{C}$			30	70		mA
V_F^*	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 20\text{ A}$			0.53	V	
		$T_j = 125^{\circ}\text{C}$			0.42	0.49		
		$T_j = 25^{\circ}\text{C}$		$I_F = 40\text{ A}$				0.69
		$T_j = 125^{\circ}\text{C}$			0.6	0.7		

Pulse test : * $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :
 $P = 0.28 \times I_{F(AV)} + 0.0105 I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

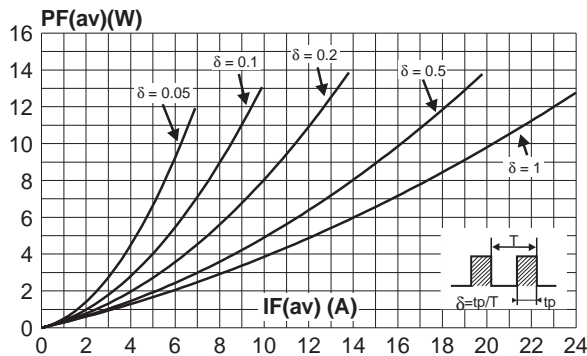


Fig. 3: Normalized avalanche power derating versus pulse duration.

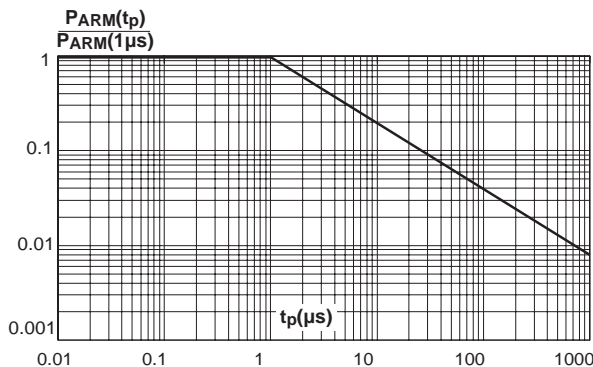


Fig. 2: Average current versus ambient temperature ($\delta = 0.5$, per diode).

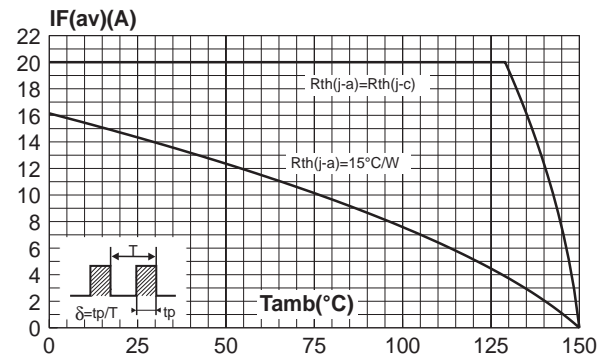


Fig. 4: Normalized avalanche power derating versus junction temperature.

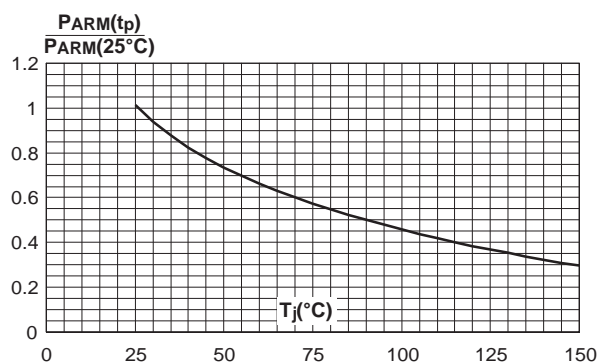


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

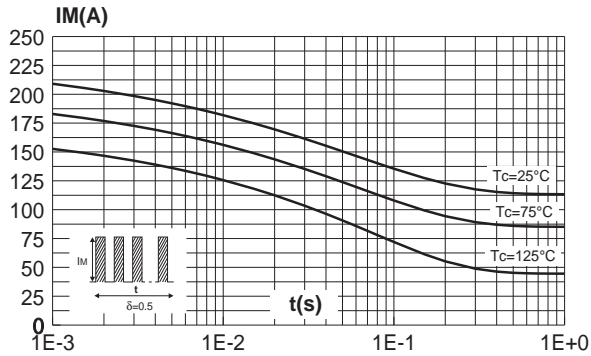


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

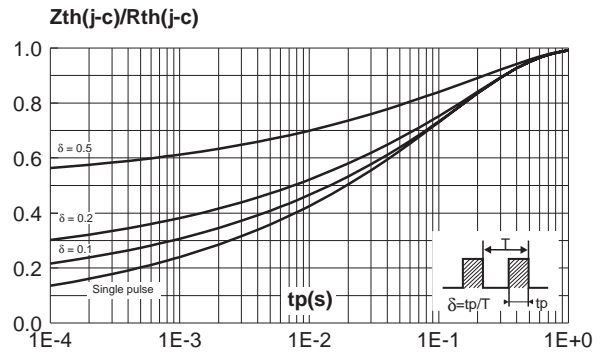


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values, per diode).

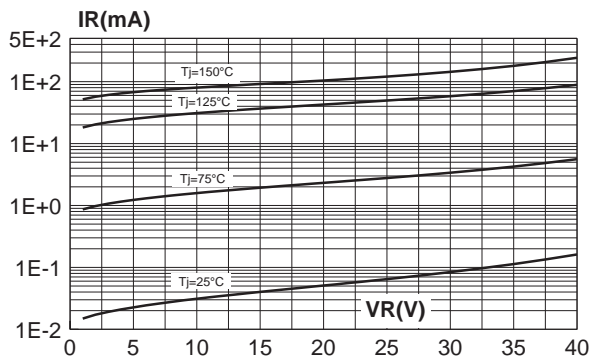


Fig. 8: Junction capacitance versus reverse voltage applied (typical values, per diode).

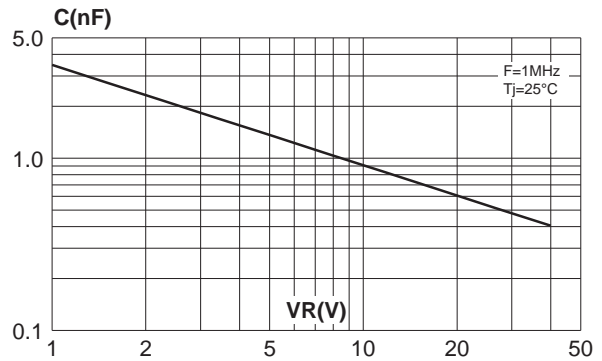
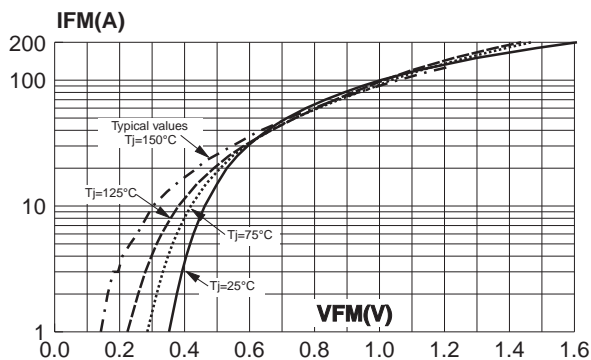
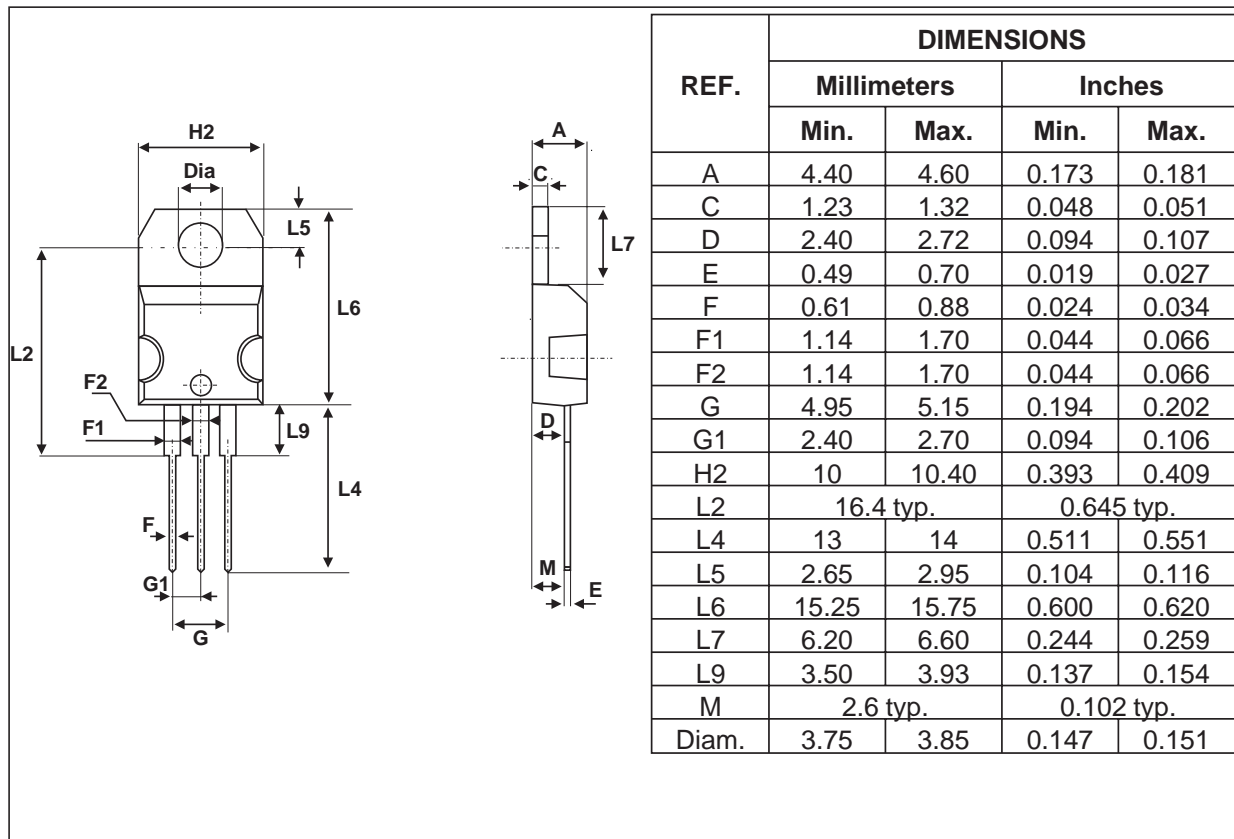


Fig. 9: Forward voltage drop versus forward current (maximum values, per diode).



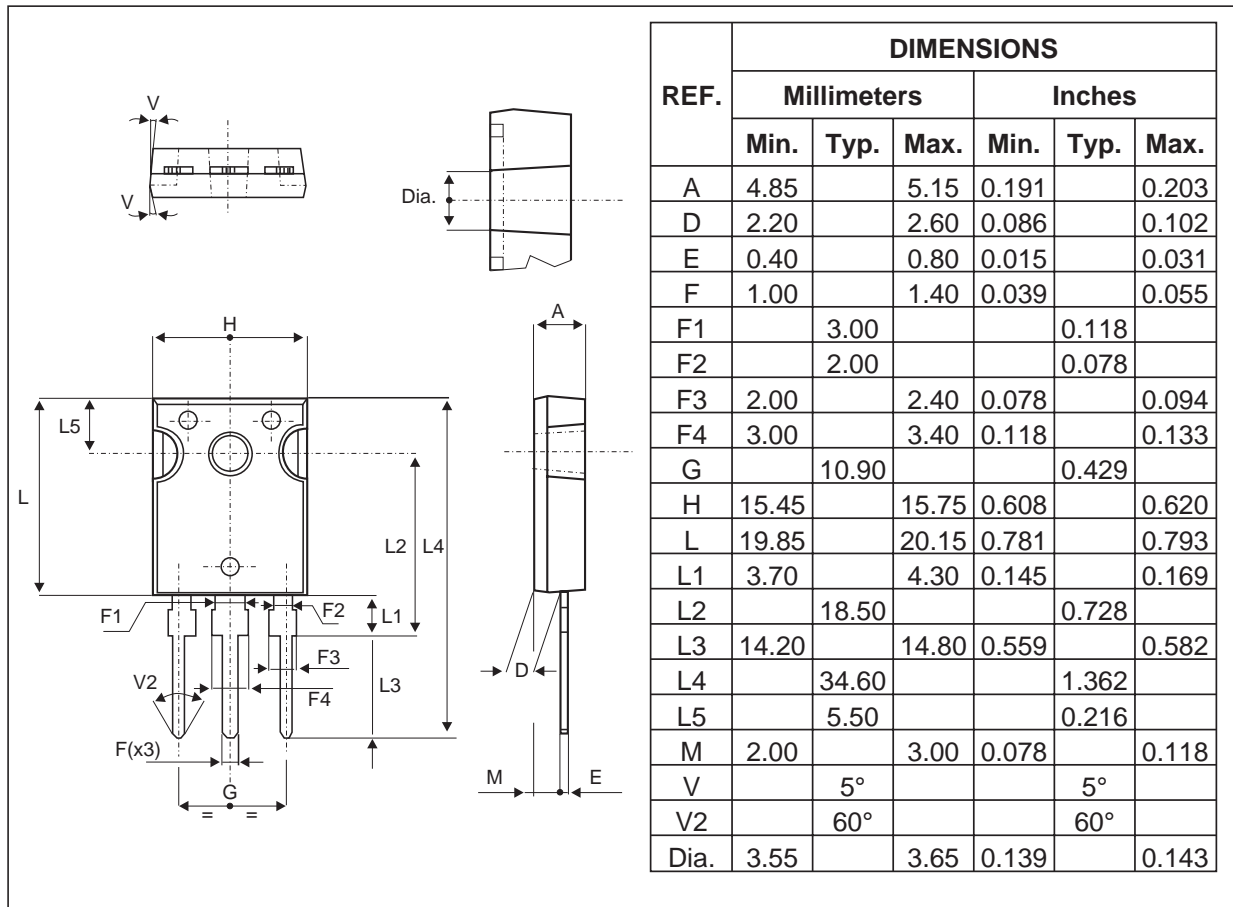
STPS40L40CT/CW

PACKAGE MECHANICAL DATA TO-220AB



- COOLING METHOD : C
- RECOMMENDED TORQUE VALUE : 0.55M.N
- MAXIMUM TORQUE VALUE : 0.70 M.N

PACKAGE MECHANICAL DATA
TO-247



- COOLING METHOD : C
- RECOMMENDED TORQUE VALUE : 0.8M.N
- MAXIMUM TORQUE VALUE : 1.0M.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS40L40CT	STPS40L40CT	TO-220AB	2g	50	Tube
STPS40L40CW	STPS40L40CW	TO-247	4.4g	30	Tube

- EPOXY MEETS UL94,V0

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